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FORM PTO 1449 (MINISTER PATENTS AND PUBLICATIONS FOR LIST OF PATENTS INFORMATION DISCLOSURE ATTY. DOCKET NO. SERIAL NO. FIS9-2003-0235US1 .10/707,841 **APPLICANT:** Haining S. Yang, et al. (Use several sheets if necessary) FILING DATE: **GROUP:** Unassigned V) REFERENCE DESIGNATION **U.S. PATENT DOCUMENTS EXAMINER DOCUMENT** FILING DATE **INITIALS** NUMBER. **DATE** NAME **CLASS** SUBCLASS (IF APPRO.) /JC/ 6,228,694 B1 5/8/2001 Doyle et al. 6,406,973 B1 6/18/2002 Lee 6,281,532 B1 8/28/2001 Doyle et al. 5,683,934 11/4/97 Candelaria 6,368,931 B1 4/9/2002 Kuhn, et al. 5,310,446 Konishi et al. 5/10/94 4,853,076 8/1/89 Tsaur et al. US 2002/0090791 A1 7/11/2002 Doyle et al. US 2002/0074598 A1 6/20/2002 Doyle et al. 6,509,618 B2 Jan et al. 6,476,462 B2 11/5/2002 Shimizu et al. /JC/ 6,362,082 B1 3/26/2002 Doyle et al. /JC/ 5,565,697 10/15/96 Asakawa et al. US 2003/0040158 A1 2/27/2003 Saitoh US 2002/0086472 A1 7/4/2002 Roberds et al. 6,521,964 B1 2/18/2003 Jan et al. /JC/ 6,506,652 01/14/03 Jan, et al. FOREIGN PATENT DOCUMENTS **DOCUMENT** TRANSLATION **NUMBER** SUBCLASS **COUNTRY CLASS** DATE YES NO OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) EXAMINER DATE CONSIDERED 02/04/2008

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Page 2 IAN 7 2 2004 FORM PTO-1448 (Modified) ATTY. DOCKET NO. SERIAL NO. LIST OF PATENTS AND PUBLICATIONS FOR FIS9-2003-0235US1 10/707/841 APPLICANT: APPLICANT'S INFORMATION DISCLOSURE Haining S. Yang, et al. **STATEMENT** (Use several sheets if necessary) FILING DATE: GROUP: 2813 **Unassigned** 01/16/2004: REFERENCE DESIGNATION **U.S. PATENT DOCUMENTS EXAMINER DOCUMENT** FILING DATE **INITIALS** NUMBER DATE NAME **CLASS** SUBCLASS (IF APPRO.) 5,081,513 /JC/ 1/14/1992 Jackson, et al. 3,602,841 8/31/1971 McGroddy 6,531,740 3/11/2003 Bosco, et al. 6,531,369 3/11/2003 Ozkan, et al. 6,501,121 12/31/2002 Yu, et al. 6,498,358 12/24/2002 Lach, et al. 6,493,497 12/10/2002 Ramdani, et al. 6,403,975 6/11/2002 Brunner, et al. 6,361,885 3/26/2002 Chou 6,255,169 7/3/2001 Li, et al. 6/12/2001 6,246,095 Brady, et al. 6,165,383 12/26/2000 Chou 6,133,071 10/17/2000 Nagai 4/4/2000 6,046,464 Schetzina /JC/ 6,025,280 2/15/2000 Brady, et al. FOREIGN PATENT DOCUMENTS **DOCUMENT** TRANSLATION **NUMBER SUBCLASS DATE COUNTRY CLASS** YES NO

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